

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L14	332	(MOS NMOS PMOS CMOS MOSFET) and memory adj array and (poly adj Si polysilicon) near3 gate and ("SiO.sub.2" silicon adj (oxide dioxide)) near3 gate adj (dielectric insulator insulating) and (RAM DRAM SRAM)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/26 11:53
L15	82	l14 and (@ad<"20000628"@rlad<"20000628")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/26 11:53
S42	39	("3849204" "3923559" "4027380" "4113514" "4151007" "4212100" "4239554" "4290825" "4331486" "4352835" "4435896" "4542512" "4620211" "4796081" "4936781" "4962065" "4992840" "5059551" "5162892" "5179029" "5198880" "5248348" "5250446" "5254506" "5264724" "5320975" "5434440" "5514628" "5571339" "5693961" "5711998" "5744202" "5822175" "5830575" "5864161" "5872387" "6023093" "6147014" "6328801").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/03/25 11:14
S43	2	("6147014").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/25 12:13
S44	177	MOSFET and gate near3 (poly polysilicon) and gate adj ((dielectric insulator) near2 (oxide silicon adj oxide SiO "SiO.sub.2" "SiO.sub.x") oxide) same (PECVD plasma adj CVD)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:30

S45	94	S44 and (@ad<"20000628"@rlad<"20000628")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:32
S46	37	MOSFET and gate near3 (poly polysilicon) and gate adj ((dielectric insulator) near2 (oxide silicon adj oxide SiO "SiO.sub.2" "SiO.sub.x") oxide) with (PECVD plasma adj CVD)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:34
S47	19	S46 and (@ad<"20000628"@rlad<"20000628")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:35
S48	15	("4141022" "5413948" "5607872" "5658813" "5739549" "5956579" "5981365" "6022765" "6037197" "6080606" "6118139" "6133073" "6146928" "6191017" "6210998").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/03/25 12:51
S49	8	(257/E21.489).OCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/25 12:55
S50	0	(257/E21.491).OCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/25 12:55
S51	4	kauffman same (SiO silicon adj (dioxide oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:55
S52	14	kauffman and MOSFET and (SiO silicon adj (dioxide oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:55

S53	120	MOSFET and (hydrogen H) adj2 ion same (SiO silicon adj (dioxide oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:55
S54	155	MOSFET and (hydrogen H) adj2 ion same (SiO gate adj oxide silicon adj (dioxide oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:55
S55	63	S54 and (@ad<"20000628" @rlad<"20000628")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:55
S56	33	kauffman adj ion	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:55
S57	1122	(hydrogen H) adj2 ion same (SiO gate adj oxide silicon adj (dioxide oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:55
S58	523	S57 and (@ad<"20000628" @rlad<"20000628")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:55
S59	437	(hydrogen H) adj2 ion with (SiO gate adj oxide silicon adj (dioxide oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:55
S60	256	S59 and (@ad<"20000628" @rlad<"20000628")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:55
S61	182	(438/ FOR.448).OCLS	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/25 12:55

S62	0	(438/ FOR448).CQLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/25 12:55
S63	180	S61 and (@ad<"20000628" @rlad<"20000628")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:55
S64	39	((hydrogen H) adj2 ion "H. sup.+ " "H.sup.2+ ") near6 plasma same (SiO gate adj oxide silicon adj (dioxide oxide)) and (gate MOSFET FET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:55
S65	22	S64 and (@ad<"20000628" @rlad<"20000628")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:55
S66	28	(david near3 chapek).in.	US-PGPUB; USPAT; USOCR	OR	ON	2008/03/25 12:55
S67	304	(257/ E21.212).CQLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/25 12:55
S68	509	(438/ 798).CQLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/25 12:55
S69	459	(438/ 783).CQLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/25 12:55
S70	177	S67 and (@ad<"20000628" @rlad<"20000628")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/25 12:55

3/ 26/ 2008 12:28:04 PM

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